

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

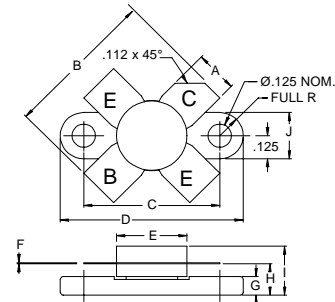
The **ASI BLW86** is Designed for Class C, 28 V High Band Applications up to 175 MHz.

FEATURES:

- Common Emitter
- $P_G = 7.0$ dB at 40 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|---------------|----------------------|
| I_C | 5.0 A |
| V_{CB0} | 65 V |
| V_{CE0} | 35 V |
| V_{EBO} | 4.0 V |
| P_{DISS} | 60 W @ $T_C = 25$ °C |
| T_J | -65 °C to +200 °C |
| T_{STG} | -65 °C to +150 °C |
| θ_{JC} | 2.9 °C/W |

PACKAGE STYLE .380 4L FLG


| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | .220 / 5.59 | .230 / 5.84 |
| B | .785 / 19.94 | |
| C | .720 / 18.29 | .730 / 18.54 |
| D | .970 / 24.64 | .980 / 24.89 |
| E | | .385 / 9.78 |
| F | .004 / 0.10 | .006 / 0.15 |
| G | .085 / 2.16 | .105 / 2.67 |
| H | .160 / 4.06 | .180 / 4.57 |
| I | | .280 / 7.11 |
| J | .240 / 6.10 | .255 / 6.48 |

CHARACTERISTICS $T_C = 25$ °C

| SYMBOL | TEST CONDITIONS | | | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-------------------|------------------|------------------|---------------|---------|---------|---------|---------|
| BV_{CEO} | $I_C = 200$ mA | | | 35 | | | V |
| BV_{CES} | $I_C = 200$ mA | | | 65 | | | V |
| BV_{CBO} | $I_C = 10$ mA | | | 65 | | | V |
| BV_{EBO} | $I_E = 10$ mA | | | 4.0 | | | V |
| I_{CBO} | $V_{CB} = 30$ V | | | | | 1.0 | mA |
| I_{CES} | $V_{CE} = 30$ V | | | | | 10 | mA |
| h_{FE} | $V_{CE} = 5.0$ V | $I_C = 500$ mA | | 5.0 | | 200 | --- |
| C_{ob} | $V_{CB} = 30$ V | $f = 1.0$ MHz | | | | 65 | pF |
| P_G η_C | $V_{CE} = 28$ V | $P_{IN} = 7.0$ W | $f = 175$ MHz | 7.6 | 60 | | dB % |